



CNR-SPIN (Genova, Italy)

HYBRID JOSEPHSON JUNCTIONS BASED ON InSb NANOFLAGS

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Outline

- ▶ InSb nanoflags for advanced devices
- ▶ InSb nanoflag Josephson junctions
- ▶ Superconducting diode in a single Josephson junction
- ▶ SQUID based on InSb nanoflags



Università
di Genova

New J. Phys. 20 (2018) 080201

<https://doi.org/10.1088/1367-2630/aad1ea>

QuantumManifesto

A New Era of Technology

May 2016

New Journal of Physics

The open access journal at the forefront of physics

ROADMAP

The quantum technologies roadmap: a European community view

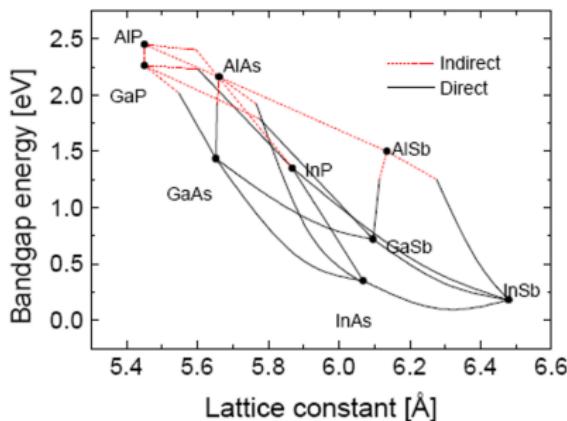
Antonio Acín^{1,2}, Immanuel Bloch^{3,4}, Harry Buhrman⁵, Tommaso Calarco⁶, Christopher Eichler⁷, Jens Eisert⁸, Daniel Esteve⁹, Nicolas Gisin¹⁰, Steffen J Glaser¹¹, Fedor Jelezko¹², Stefan Kuhr¹³, Maciej Lewenstein¹⁴, Max F Riedel¹⁵, Piet O Schmidt^{13,14}, Rob Thew¹⁶, Andreas Wallraff¹⁷, Ian Walmsley¹⁸ and Frank K Wilhelm¹⁶

Low temperature superconducting electronics

InSb semiconductor

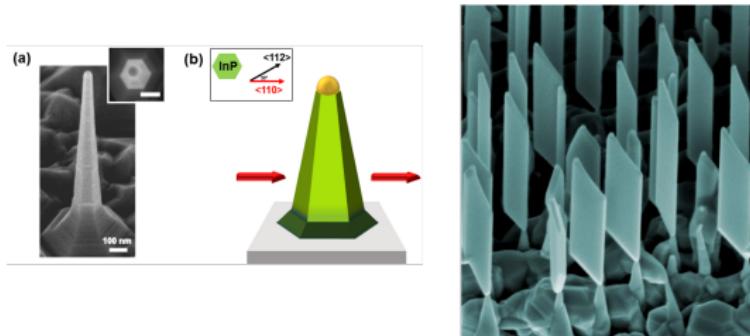
Why InSb?

- ▶ narrow bandgap $0.23\text{eV} \rightarrow$ mid-IR optoelectronics
- ▶ high bulk mobility $7.7 \cdot 10^4 \text{cm}^2/(\text{Vs}) \rightarrow$ high-speed electronic devices
- ▶ small effective mass $m = 0.018m_e \rightarrow$ low power electronic devices
- ▶ strong spin orbit interactions $E_{SOI} \sim 200\mu\text{eV}$ $g \sim 50 \rightarrow$ spintronics and topological devices



InSb nanoflags

InSb: challenging to grow 2D quantum wells
→ novel approach: 2D nanoflags

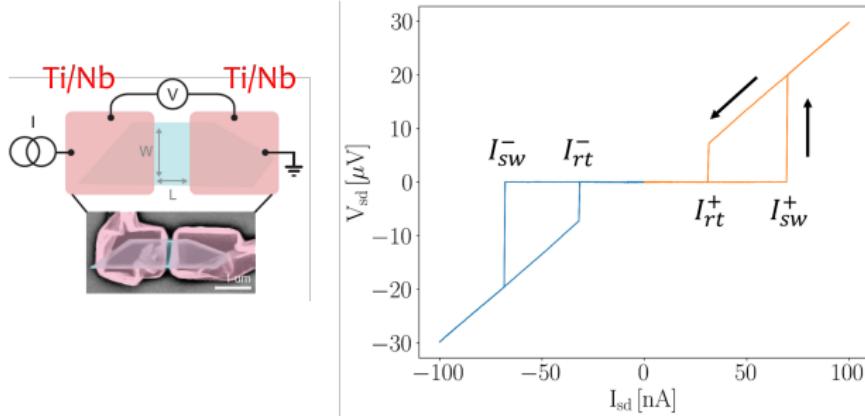


Tapered nanowires are used as stems

- ▶ length $\sim 2\mu\text{m}$
- ▶ width $\sim 700\text{nm}$
- ▶ thickness $\sim 100\text{nm}$
- ▶ defect-free structure
- ▶ mobility $\sim 29500\text{cm}^2/(\text{Vs})$
- ▶ mean free path $l_e \sim 500\text{nm}$

InSb Josephson junctions

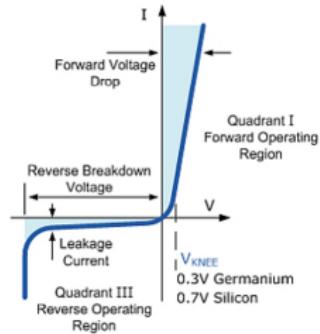
InSb nanoflag SNS devices



- Nb superconducting contacts $\Delta \sim 1.3\text{meV} \rightarrow \Delta^* \sim 250\mu\text{eV}$
- length $\sim 200\text{nm}$ and width $\sim 700\text{nm}$
- ballistic regime $I \ll I_e$
- high transparency $\tau \sim 0.9$

Diodes

The *pn* junction is at the basis of conventional electronics



Is it possible to obtain an analog for superconducting circuits?

Breaking of both time-reversal and inversion symmetry!

SDE experiments

Article

Observation of superconducting diode effect

<https://doi.org/10.1038/s41586-020-2590-4> Fuyuki Ando¹, Yuta Miyasaka², Tian Li², Jun Ishizuka², Tomonori Arakawa^{3,4}, Yoichi Shioya⁵

Fuyuki Ando¹, Yuta Miyazaka¹, Tian Li¹, Jun Ishizuka², Tomonori Arakawa^{3,4}, Yoichi Shiota

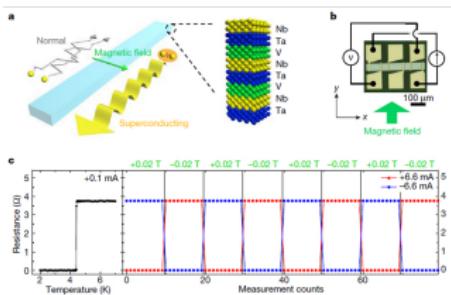
Received: 14 March 2020

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Nonlinear optical and electrical effects associated with a lack of spatial inversion symmetry allow direction-selective propagation and transport of quantum particles such as photons¹ and electrons²⁻⁹. The most common example of such nonreciprocal



F. Ando et al., Nature 584 (2020) 373.

nature
nanotechnology

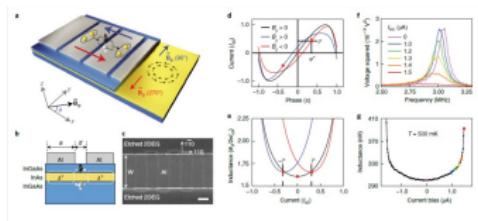
ARTICLES

<https://doi.org/10.1080/02500233.2020.1732322>



Supercurrent rectification and magnetochiral effects in symmetric Josephson junctions

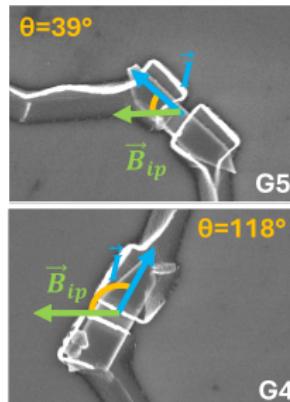
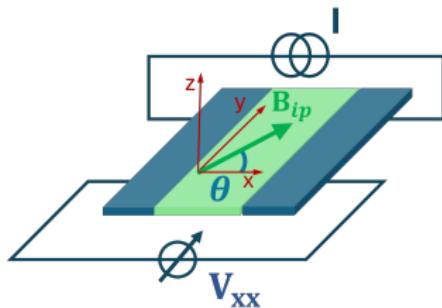
Christian Baumgartner¹³, Lorenz Fuchs¹³, Andreas Costa¹², Simon Reinhardt¹¹, Sergei Gronin^{3,4}, Geoffrey C. Gardner^{1,4}, Tyler Lindemann^{4,5}, Michael J. Manfra^{3,4,5,6,7}, Paulo E. Faria Junior², Denis Kochan², Jaroslav Fabian¹², Nicola Paradiso^{1,2*} and Christoph Strunk^{1,1}



C. Baumgartner et al., Nat. Nano 17 (2022) 39.

SDE in a single Josephson junction

InSb nanoflag planar Josephson junction



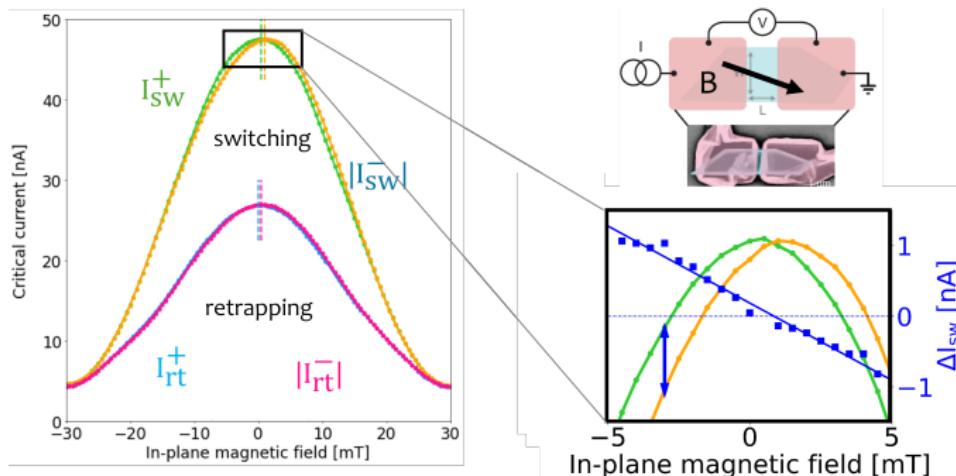
need for a planar B field

Turini et al NanoLetters 2022

Josephson diode effect

Supercurrent at 30mK

I_{SW}^{\pm} switching current in opposite bias directions

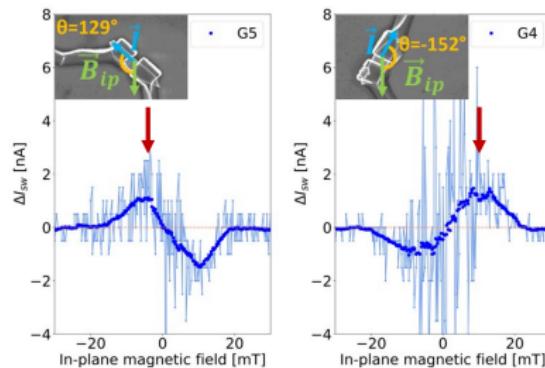


JDE is driven by magnetic field!

Supercurrent asymmetry

$$\Delta I_{SW} = I_{SW}^+ - |I_{SW}^-|$$

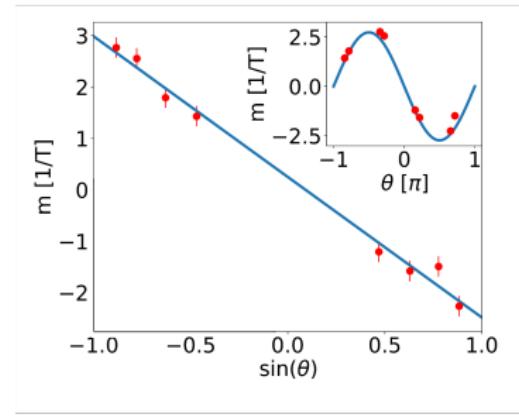
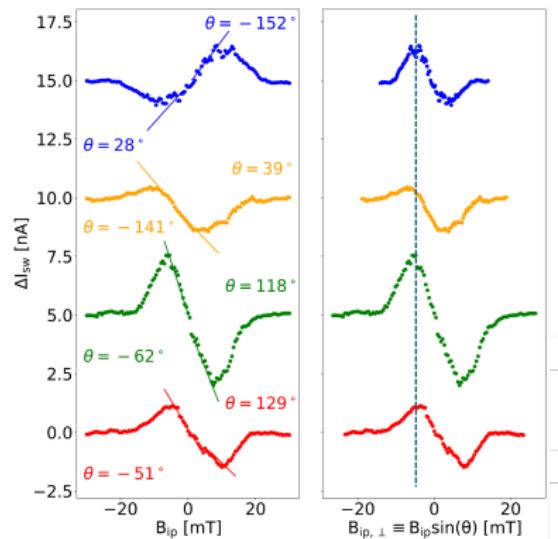
in-plane B_{ip} field dependence



- ▶ anti-symmetric in B
- ▶ linear behaviour around $B = 0$
- ▶ rounded maxima
- ▶ suppression above ~ 20 mT

Angle dependence

JDE depends on the planar angle $\theta \rightarrow$ Rashba SOI

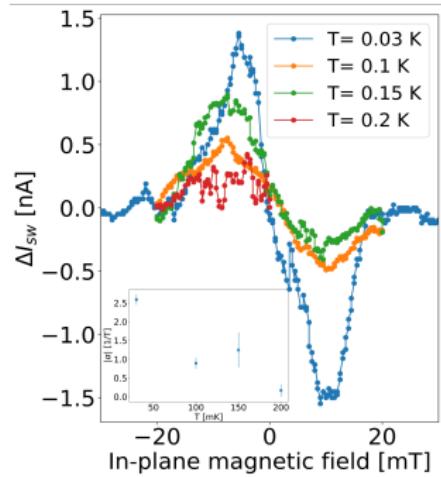


$$\eta = \frac{\Delta I_{SW}}{I_{SW}^+ + |I_{SW}^-|} = m B_{ip}$$

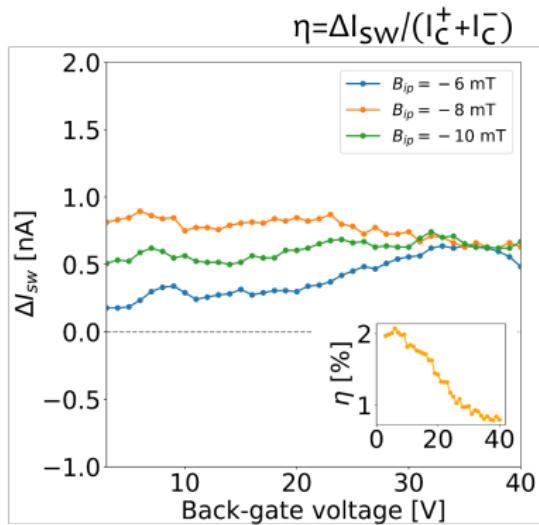
linear coefficient $m \propto \sin(\theta)$

Extrinsic parameters

JDE temperature dependence



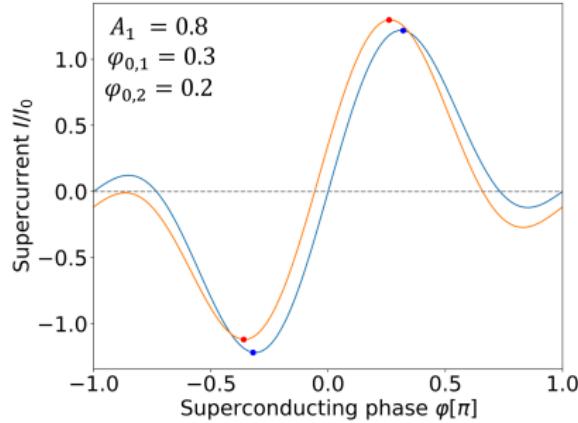
JDE gate-voltage dependence



JDE interpretation

- ballistic and short junction regime
- dominant Rashba SOI
- finite momentum pairing $q = g\mu_B B/v_F$
- high transparency $\tau \rightarrow$ skewed CPR

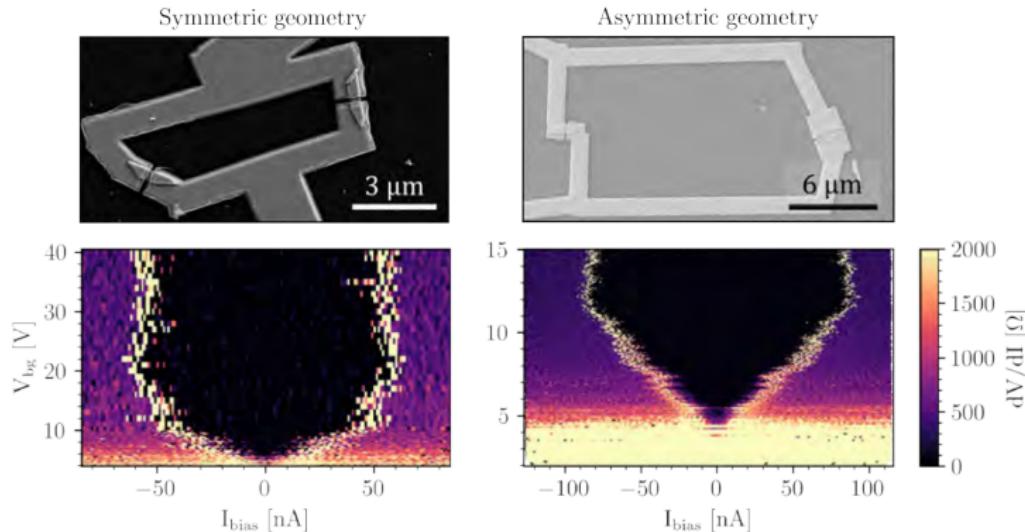
$$I = I_0 \sum_n c_n \sin(n\phi)$$



SQUID based on InSb nanoflags

How to inspect the CPR content?

SQUID with different geometries



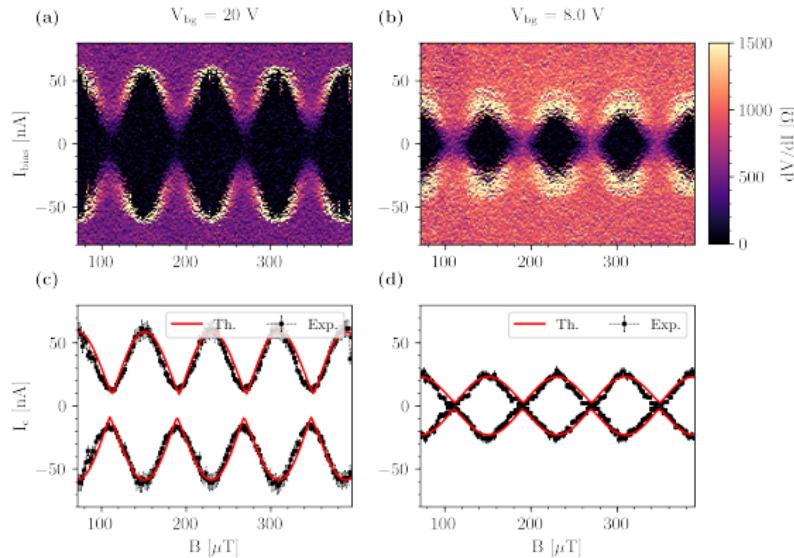
$$A_{geo}^{\text{sym}} = 13.6 \mu\text{m}^2 \quad A_{geo}^{\text{asym}} = 118 \mu\text{m}^2$$

Chieppa et al, ArXiv 2025

SQUID response

$$I_{C, \text{ SQUID}} = \text{Max}_\varphi \left[I_1(\varphi) + I_2(\varphi - 2\pi \frac{\Phi}{\Phi_0}) \right]$$

Interference patterns in the symmetric geometry



High transparency τ at high V_{bg}

Numerical simulations

Effective two band model for InSb

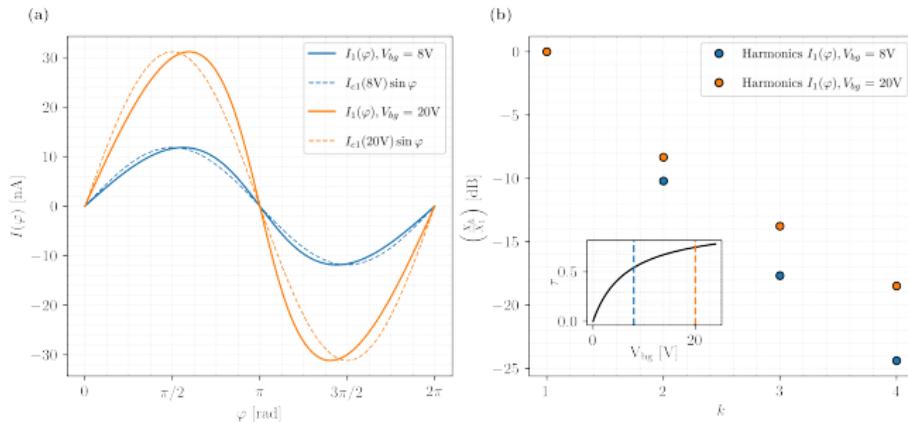
$$\mathcal{H}(\vec{k}) = \left(\frac{\hbar^2 \vec{k}^2}{2m^*} - \mu \right) \sigma_0 - \alpha_R k_y \sigma_x + \alpha_R k_x \sigma_y + \frac{g\mu_B}{2} B \sigma_z$$

- Bogoliubov-de Gennes formalism with Δ induced SC gap
- Tight-binding simulation
- SQUID geometry with two parallel Josephson junctions
- Recursive Green function method

Chieppa et al, ArXiv (2025)

Skewed CPR

CPR of a single junction with different V_{bg}
Major skewness at high back-gate



JJ transparency modulated with V_{bg}

$$\tau = \frac{1}{1 + z^2(V_{bg})}$$

Conclusions

- ▶ InSb nanoflag based Josephson junction
- ▶ Josephson diode effect
- ▶ SQUID based on InSb nanoflags
- ▶ High harmonic contents and skewed CPRs

B. Turini et al, NanoLetters **22**, 8502 (2022)



A. Chieppa et al., ArXiv:2504.**** (2025)



Collaborations and projects

- ▶ **CNR-NANO:** S. Heun, L. Sorba, F. Giazotto, E. Strambini, V. Zannier, I. Verma, A. Crippa, S. Salimian, A. Iorio, B. Turini, A. Chieppa
- ▶ **Univ. Genova:** M. Sasetti, N. Traverso Ziani, S. Traverso, S. Fracassi

Project PRIN 2022 (MUR, Italy): "Topoflags"

